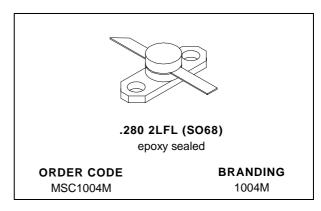


MSC1004M

RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

- 1025 1150 MHz
- RUGGEDIZED VSWR ∞:1
- INTERNAL INPUT MATCHING
- LOW THERMAL RESISTANCE
- P_{OUT} = 4.0 W MIN. WITH 9.0 dB GAIN

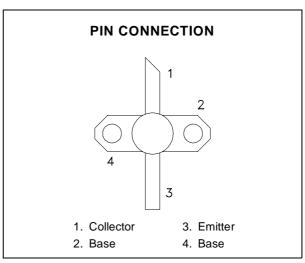


DESCRIPTION

The MSC1004M is a low-level Class C pulsed transistor specifically designed for DME/IFF driver or output applications.

These devices are capable of withstanding a ∞:1 load VSWR at any phase angle under full rated conditions. Low RF thermal resistance and automatic bonding techniques ensure high reliability and product consistency.

The MSC1004M is housed in the IMPAC™ package with internal input matching.



ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit	
P _{DISS}	Power Dissipation* (T _C ≤ 100°C)	18	W	
Ic	Device Current* 65		mA	
Vcc	Collector-Supply Voltage*	32	V	
TJ	Junction Temperature	200	°C	
T _{STG}	Storage Temperature	- 65 to +150	°C	

THERMAL DATA

R _{TH(j-c)} Junction-Case Thermal Resistance*	5	°C/W
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^{*}Applies only to rated RF amplifier operation

June 12, 1995

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

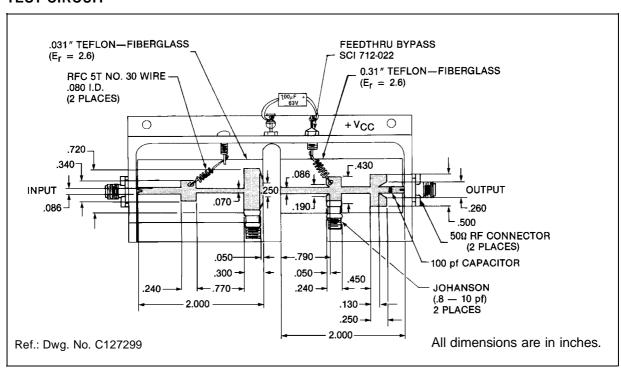
Symbol	Test Conditions	Value			IIm:4		
	rest Conditions		Min.	Тур.	Max.	Unit	
ВУсво	I _C = 1 mA	$I_E = 0 \text{ mA}$		45	_	-	V
BVCER	I _C = 5 mA	$R_{BE} = 10 \Omega$		45	_	_	V
BV _{EBO}	I _E = 1 mA	$I_C = 0mA$		3.5	_		V
I _{CES}	V _{CE} = 28 V				_	1.0	mA
h _{FE}	V _{CE} = 5 V	I _C = 200 mA		30	_	300	_

DYNAMIC

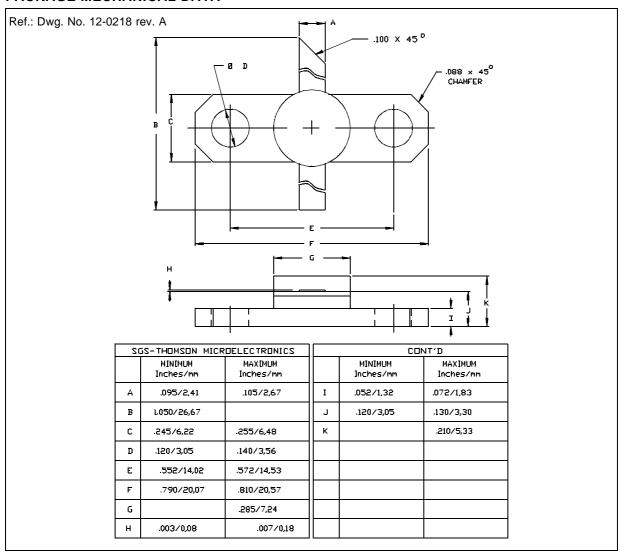
Symbol	Test Conditions			Value		llm:4	
Symbol				Min.	Тур.	Max.	Unit
P _{OUT}	f = 1025 - 1150 MHz	$P_{IN}=500\ mW$	$V_{CC} = 28 \text{ V}$	4.0	_	_	W
ης	f = 1025 - 1150 MHz	$P_{IN} = 500 \text{ mW}$	V _{CC} = 28 V	35		_	%
G _P	f = 1025 - 1150 MHz	$P_{IN} = 500 \text{ mW}$	$V_{CC} = 28 \text{ V}$	9.0	_	_	dB

Note: Pulse Width = $10\mu Sec$ Duty Cycle = 1%

TEST CIRCUIT



PACKAGE MECHANICAL DATA



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